

34. (New) Structure according to Claim 22, characterized in that the thin layer (2) is made integral with a support (3) through the use of a brazing material.

35. (New) Structure according to Claim 29, characterized in that the material of the thin layer (2) is chosen from among SiC, GaAs and InP.

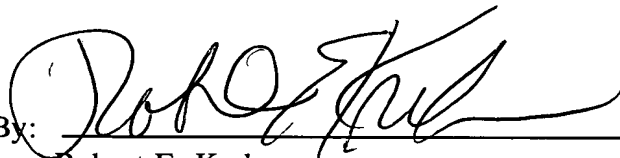
36. (New) Structure according to Claim 29, characterized in that the support (3) is made of silicon.

REMARKS

The Examiner is cordially invited to telephone the undersigned at (650) 622-2332 for any reason which would advance the instant application to allowance.

Respectfully submitted,

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23. (Amended) Structure according to [any one of Claims 20 to 22] Claim 20, characterized in that the thin layer (2) is made integral with a support (3) through an intermediate conductive surface.

26. (Amended) Structure according to [any one of Claims 23 to 25] Claim 23, characterized in that deposition of conductive bonding materials is associated with said metal interface layer.

28. (Amended) Structure according to [any one of Claims 20 to 22] Claim 22, characterized in that the thin layer (2) is made integral with a support (3) through the use of a brazing material.

30. (Amended) Structure according to any one of [Claims 20 to 29] Claim 20, characterized in that the material of the thin layer (2) is chosen from among SiC, GaAs and InP.

31. (Amended) Structure according to [any one of Claims 23 to 29] Claim 23, characterized in that the support (3) is made of silicon.

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